

Amendments to the Claims

This listing will replace all prior versions, and listing, of claims in the application.

Claims 1-24. (cancelled)

25. (currently amended) A multilevel interconnect structure, comprising:

a semiconductor surface that has been provided with metal points of electrical contact in said surface, there-
over having been created a low k compound layer of inter
metal dielectric comprising:

(1) a first layer of dielectric deposited on said semiconductor surface, said first layer of dielectric containing comprising a first network of trenches filled with air;

(2) a second layer of dielectric deposited on and in
contact with said first layer of dielectric on said
semiconductor surface, said second layer of dielectric containing comprising a second network of trenches filled with air, ~~whereby~~ said second network of trenches ~~is being~~ intersecting with in ~~physical~~ contact with and ~~intersects~~ intersecting with

said first network of trenches to form an interconnected network of trenches filled with air~~under an angle~~; and

(3) a layer of oxide deposited over said second layer of dielectric, said layer of oxide comprising:

(i) a first layer of oxide having openings created there-through, said openings being aligned with the intersections between said first and second network of trenches, enabling creation of said first and second network of trenches; and

(ii) a second layer of oxide, said second layer of oxide closing the openings in the first layer of oxide.

26. (currently amended) The multilevel interconnect structure of claim 25, ~~whereby furthermore~~ additionally a network of metal interconnects ~~interconnect lines is created on having been created over said three layers of dielectric said layer of oxide.~~

27. (currently amended) The multilevel interconnect structure of claim 25, ~~whereby furthermore~~ said layer of oxide deposited over said second layer of dielectric ~~trenches is extended in~~ having a thickness between about 1000 and 4000 Angstroms.

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28. (currently amended) The multilevel interconnect structure of claim 27 whereby furthermore a network of metal interconnect lines is created on said layer of oxide deposited over said second layer of dielectric ~~extended layer of oxide.~~